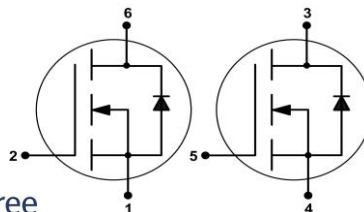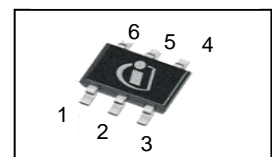# OptiMOS™2 Small-Signal-Transistor

Features

• Dual N-channel

• Enhancement mode

• Super Logic level (2.5V rated)

• Avalanche rated

• Qualified according to AEC Q101

• 100% lead-free; RoHS compliant

• Halogen-free according to IEC61249-2-21

Product Summary

V_{DS}		20	V
$R_{DS(on),max}$	V_{GS}=4.5 V	350	mΩ
	V_{GS}=2.5 V	600	
I_D		0.95	A

PG-SOT-363

Type	Package	Tape and Reel Information	Marking	Lead Free	Packing
BSD235N	PG-SOT-363	H6327: 3000 pcs/ reel	X6s	Yes	Non dry

Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter [1]	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	T_A=25 °C	0.95	A
		T_A=70 °C	0.76	
Pulsed drain current	$I_{D,pulse}$	T_A=25 °C	3.8	
Avalanche energy, single pulse	E_{AS}	I_D=0.95 A, R_{GS}=16 Ω	1.6	mJ
Reverse diode dv/dt	dv/dt	I_D=0.95 A, V_{DS}=16 V, di/dt=200 A/µs, $T_{j,max}$=150 °C	6	kV/µs
Gate source voltage	V_{GS}		±12	V
Power dissipation	P_{tot}	T_A=25 °C	0.5	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 150	°C
ESD Class		JESD22-A114 -HBM	0 (<250V)	
Soldering Temperature			260 °C	
IEC climatic category; DIN IEC 68-1			55/150/56	

[1] Remark: only one of both transistors in operation.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Thermal resistance, junction - ambient	R_{thJA}	minimal footprint[2]	-	-	250	K/W

Electrical characteristics, at T_j=25 °C, unless otherwise specified

Static characteristics

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0 V, I_D=250 µA	20	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=1.6 µA	0.7	0.95	1.2	
Drain-source leakage current	I_{DSS}	V_{DS}=20 V, V_{GS}=0 V, T_j=25 °C	-	-	1	µA
		V_{DS}=20 V, V_{GS}=0 V, T_j=150 °C	-	-	100	
Gate-source leakage current	I_{GSS}	V_{GS}=12 V, V_{DS}=0 V	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=2.5 V, I_D=0.29 A	-	415	600	mΩ
		V_{GS}=4.5 V, I_D=0.95 A	-	266	350	
Transconductance	g_{fs}	$\|V_{DS}\|$>2$\|I_D\|R_{DS(on)max}$, I_D=0.76 A		2	-	S

[2] Performed on 40 mm^2 FR4 PCB. The traces are 1mm wide, 70µm thick and 20mm long; they are present on both sides of the PCB

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics						
Input capacitance	C_{iss}	V_{GS}=0 V, V_{DS}=10 V, f=1 MHz	-	49	63	pF
Output capacitance	C_{oss}		-	23	32	
Reverse transfer capacitance	C_{rss}		-	3.2	-	
Turn-on delay time	$t_{d(on)}$	V_{DD}=10 V, V_{GS}=4.5 V, I_D=0.95 A, $R_{G,ext}$=6 Ω	-	3.8	-	ns
Rise time	t_r		-	3.6	-	
Turn-off delay time	$t_{d(off)}$		-	4.5	-	
Fall time	t_f		-	1.2	-	
Gate Charge Characteristics						
Gate to source charge	Q_{gs}	V_{DD}=10 V, I_D=0.95 A, V_{GS}=0 to 4.5 V	-	0.11	-	nC
Gate to drain charge	Q_{gd}		-	0.07	-	
Gate charge total	Q_g		-	0.32	-	
Gate plateau voltage	$V_{plateau}$		-	2.4	-	V
Reverse Diode						
Diode continous forward current	I_S	T_A=25 °C	-	-	0.5	A
Diode pulse current	$I_{S,pulse}$		-	-	3.8	
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=0.95 A, T_j=25 °C	-	0.9	1.2	V
Reverse recovery time	t_{rr}	V_R=10 V, I_F=0.95 A, di_F/dt=100 A/µs	-	5.2	-	ns
Reverse recovery charge	Q_{rr}		-	0.97	-	nC

1 Power dissipation

P_{tot}=f(T_A)
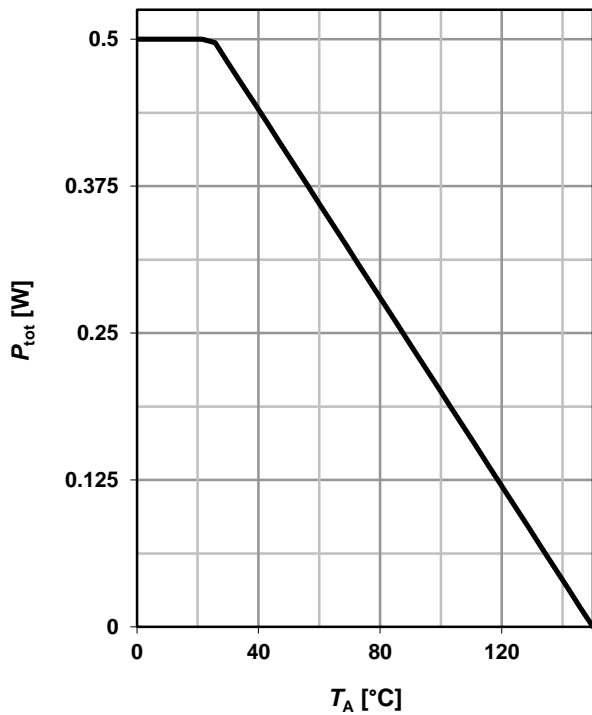
2 Drain current

I_D=f(T_A); V_{GS}≥4.5 V
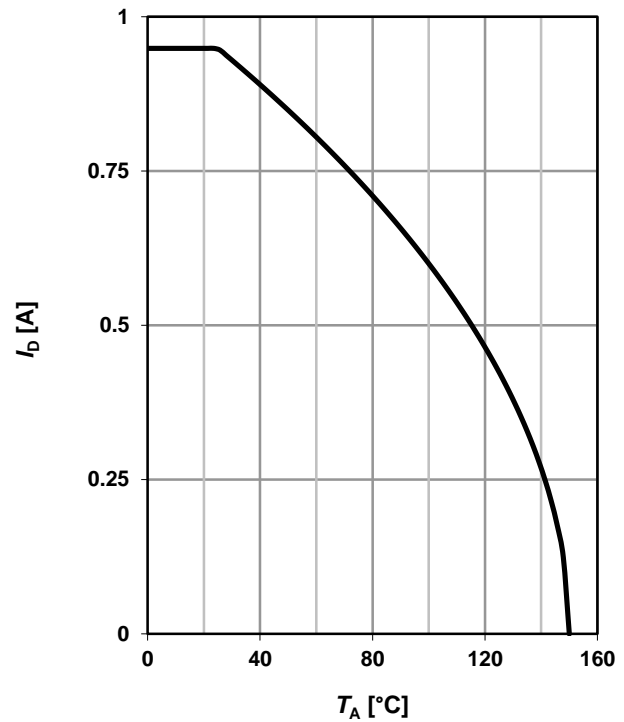
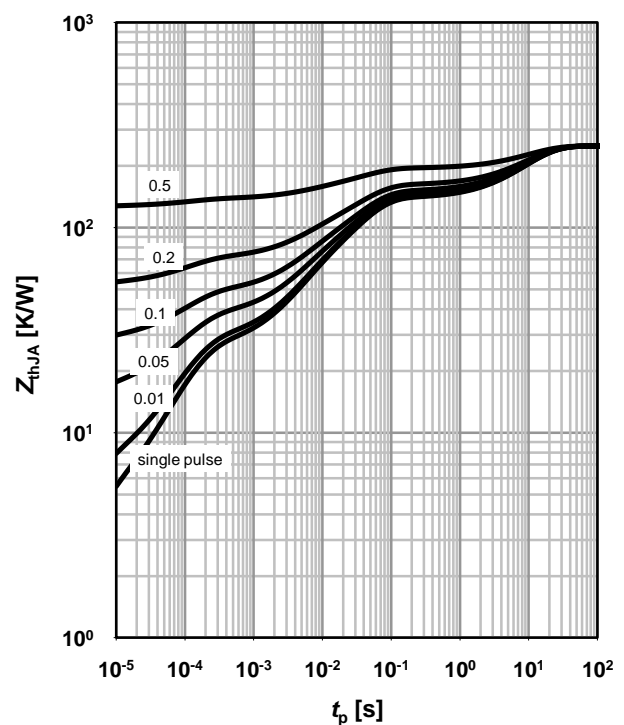## 3 Safe operating area

I_D=f(V_{DS}); T_A=25 °C; D=0

parameter: t_p
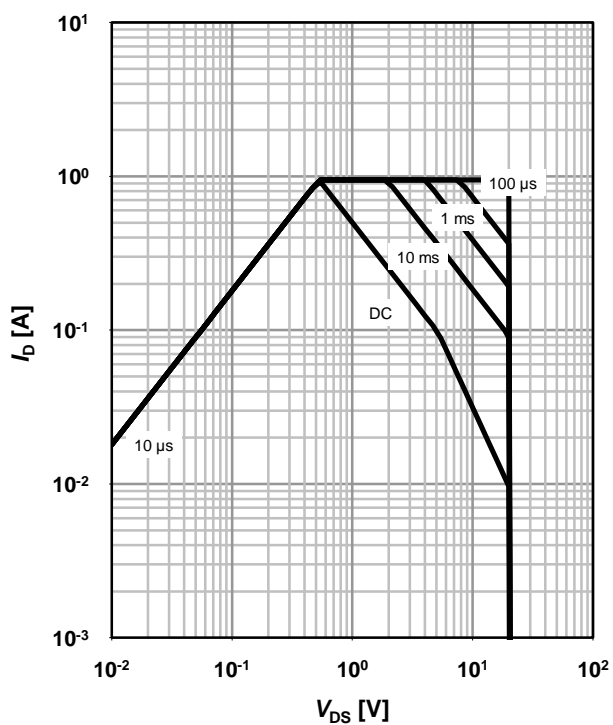
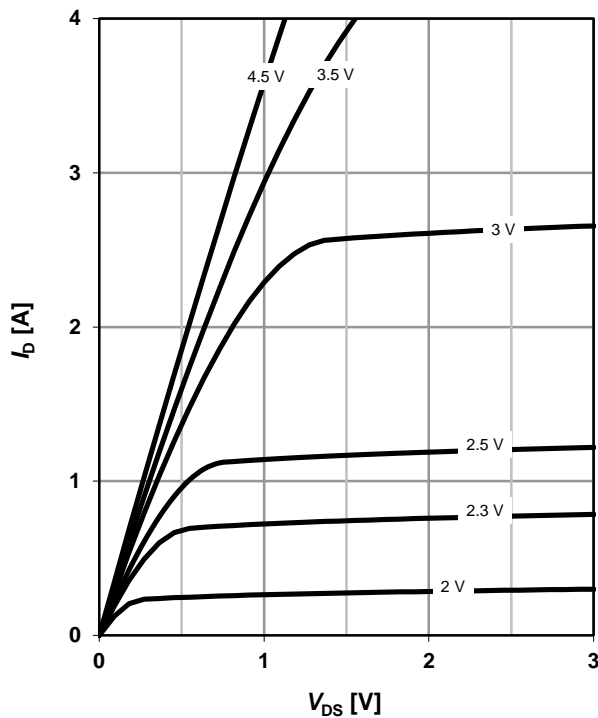## 4 Max. transient thermal impedance

Z_{thJA}=f(t_p)
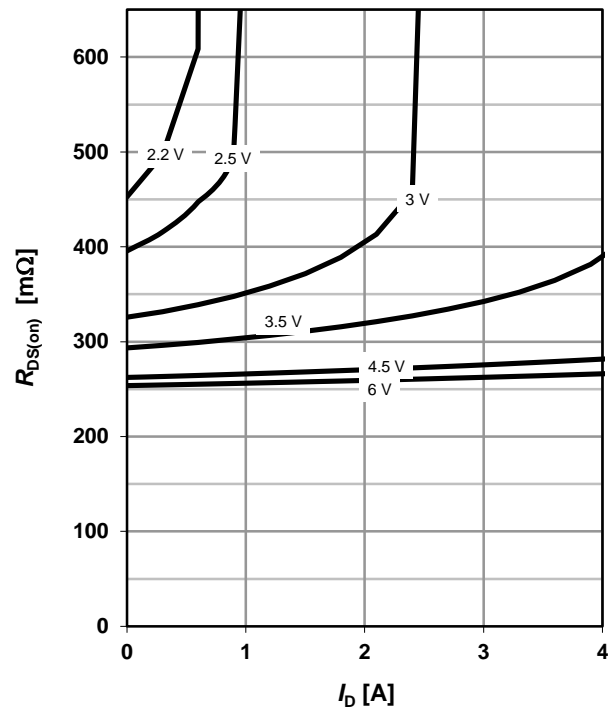
parameter: D=t_p/T

5 Typ. output characteristics

I_D=f(V_{DS}); T_j=25 °C

parameter: V_{GS}

6 Typ. drain-source on resistance

$R_{DS(on)}$=f(I_D); T_j=25 °C

parameter: V_{GS}

7 Typ. transfer characteristics
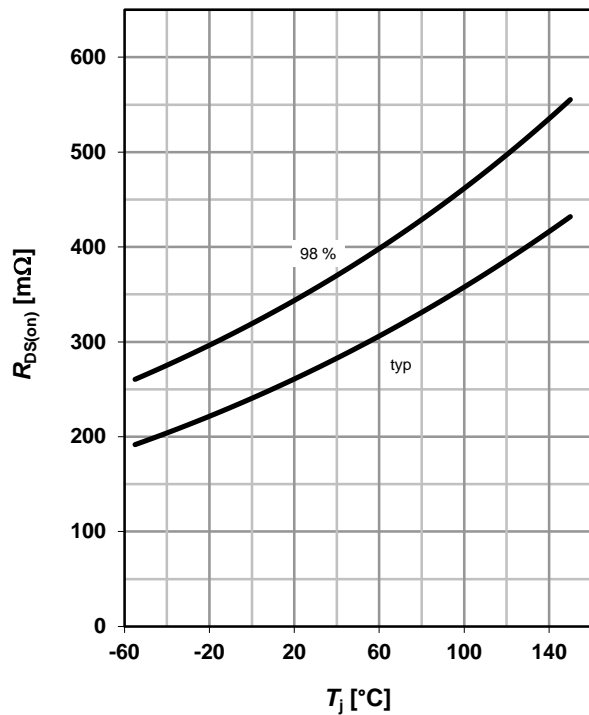
I_D=f(V_{GS}); $|V_{DS}|>2|I_D|R_{DS(on)max}$
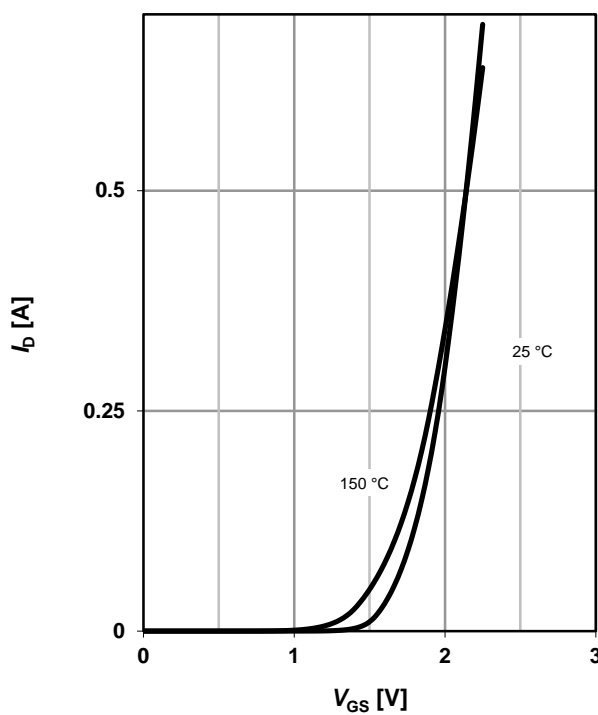
8 Typ. forward transconductance

g_{fs}=f(I_D); T_j=25 °C
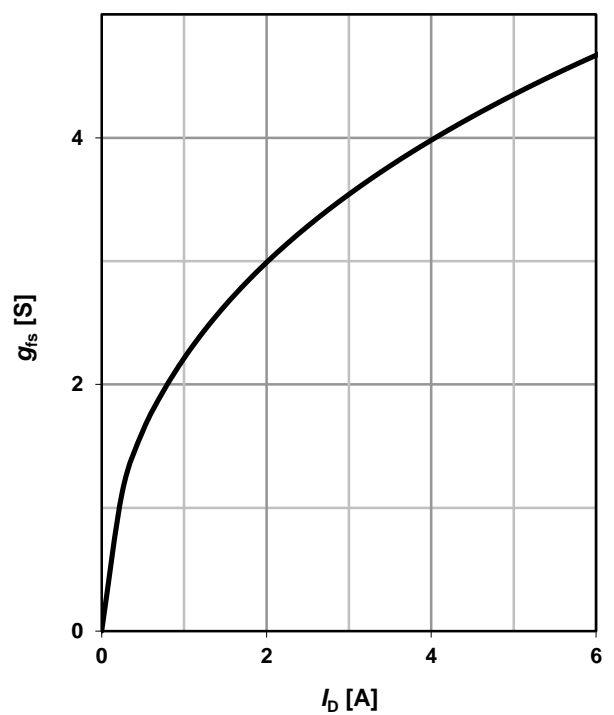
9 Drain-source on-state resistance

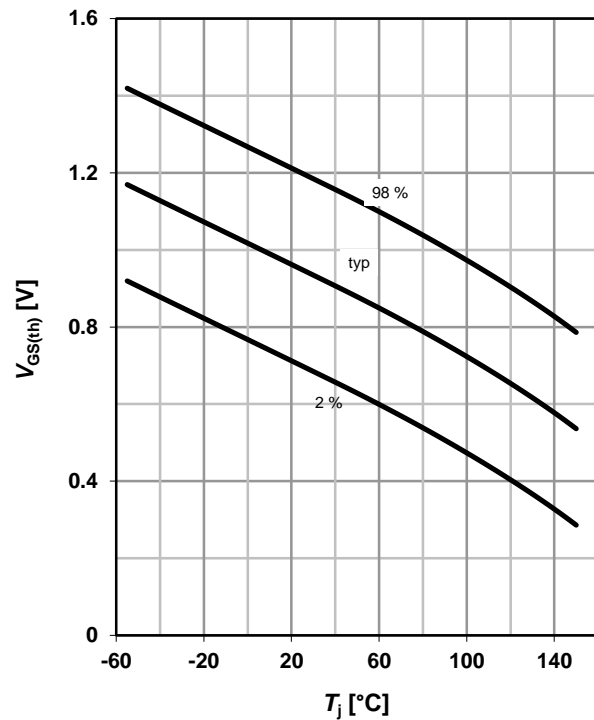$R_{DS(on)}$=f(T_j); I_D=0.95 A; V_{GS}=4.5 V

10 Typ. gate threshold voltage

$V_{GS(th)}$=f(T_j); V_{DS}=V_{GS}; I_D=1.6 µA

parameter: I_D

11 Typ. capacitances

C=f(V_{DS}); V_{GS}=0 V; f=1 MHz; T_j=25°C
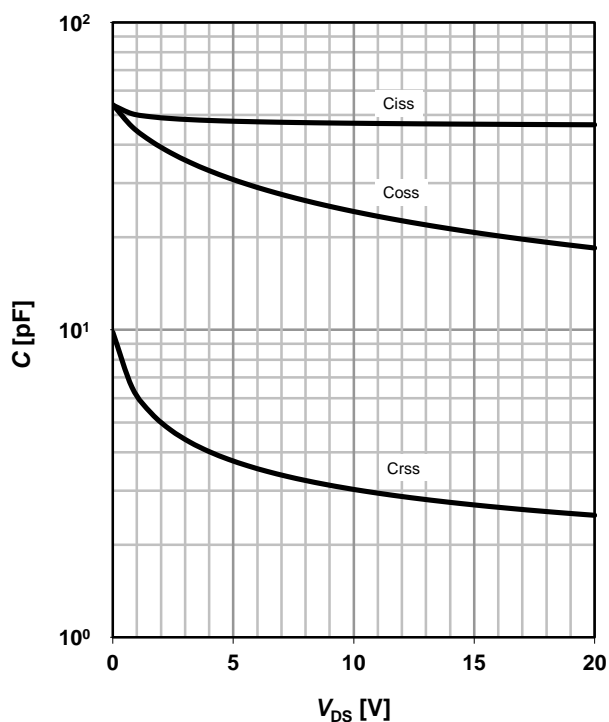
12 Forward characteristics of reverse diode
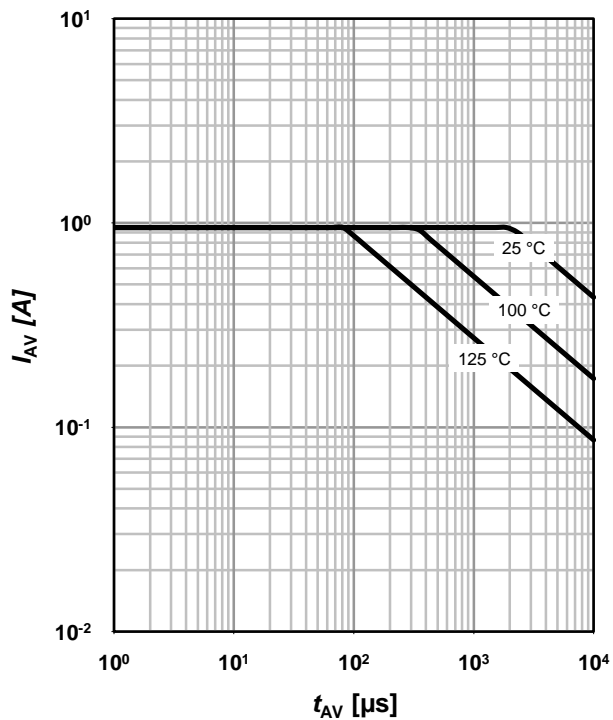
I_F=f(V_{SD})

parameter: T_j
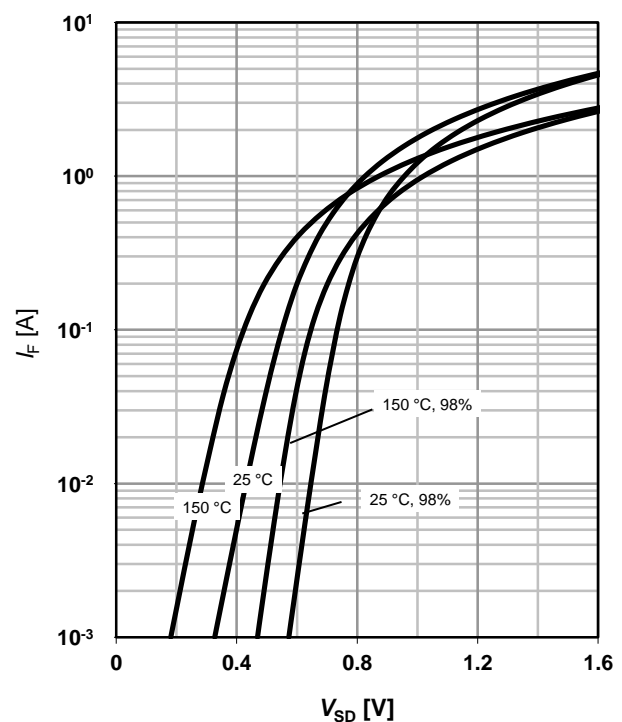
13 Avalanche characteristics
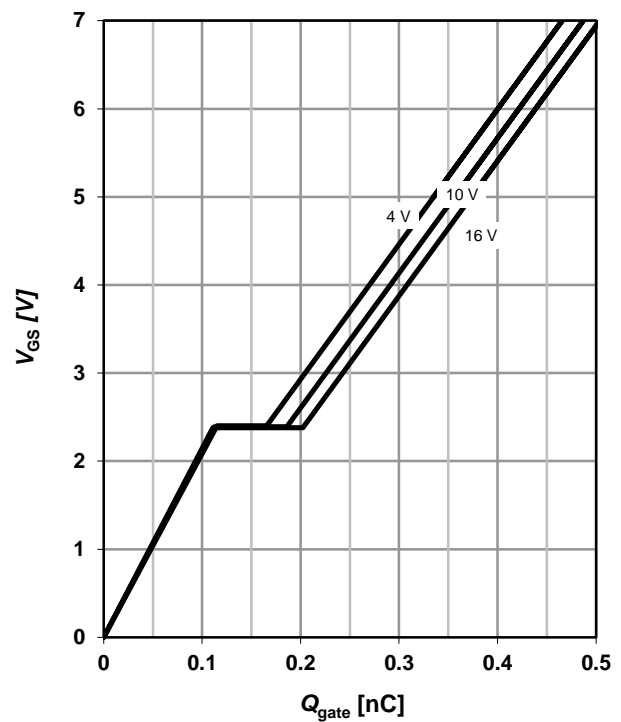
I_{AS}=f(t_{AV}); R_{GS}=16 Ω
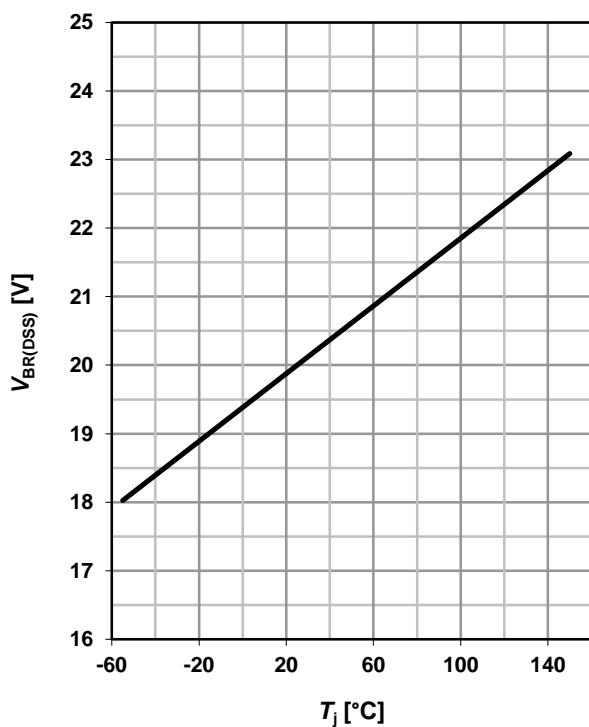
parameter: $T_{j(start)}$

14 Typ. gate charge

V_{GS}=f(Q_{gate}); I_D=0.95 A pulsed

parameter: V_{DD}

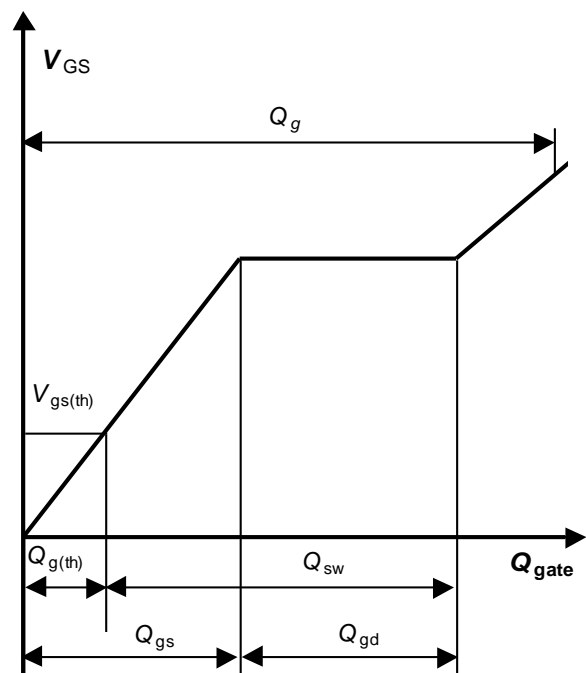## 15 Drain-source breakdown voltage

$V_{BR(DSS)}$=f(T_j); I_D=250 µA

16 Gate charge waveforms
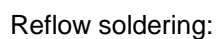
SOT-363

Package Outline:

GPS05604

Footprint:

Transport direction

HLG05827

Packing:

Pin 1 marking

CSOG5902

Reflow soldering:

HLG05826

Note: For symmetric types there is no defined Pin 1 orientation in the reel.

Dimensions in mm

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